

Schottky Diode

DSA240X200NA

V_{RRM}	=	200 V
I _{FAV}	<i>=</i> 2x	120 A
VF	=	0.87 V

High Performance Schottky Diode Low Loss and Soft Recovery Parallel legs

Part number

DSA240X200NA



Backside: isolated



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Features / Advantages:

- Very low Vf
- Extremely low switching losses
- Low Irm values
- Improved thermal behaviour
- High reliability circuit operation
 Low voltage peaks for reduced
- protection circuits
- Low noise switching

Applications:

- Rectifiers in switch mode power supplies (SMPS)
- Free wheeling diode in low voltage converters

Package: SOT-227B (minibloc)

- Isolation Voltage: 3000 V~
- Industry standard outline
- RoHS compliant
- Epoxy meets UL 94V-0
- Base plate: Copper
- internally DCB isolated
- Advanced power cycling

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Schottky	y				Rating	S	
Symbol	Definition	Conditions		min.	typ.	max.	Unit
V _{RSM}	max. non-repetitive reverse block	ing voltage	$T_{VJ} = 25^{\circ}C$			200	V
V _{RRM}	max. repetitive reverse blocking v	oltage	$T_{VJ} = 25^{\circ}C$			200	V
I _R	reverse current, drain current	$V_R = 200 V$	$T_{vJ} = 25^{\circ}C$			1.5	mA
		$V_{\rm R}$ = 200 V	$T_{v_J} = 125^{\circ}C$			15	mA
V _F	forward voltage drop	I _F = 120 A	$T_{VJ} = 25^{\circ}C$			1.00	V
		$I_{F} = 240 \text{ A}$				1.26	V
		I _F = 120 A	T _{vJ} = 125°C			0.87	V
		$I_{F} = 240 \text{ A}$				1.17	V
I FAV	average forward current	$T_c = 95^{\circ}C$	$T_{vJ} = 150$ °C			120	A
		rectangular d = 0.5					
V _{F0}	threshold voltage		$T_{vJ} = 150$ °C			0.54	V
r _F	slope resistance f Tor power ic	ss calculation only				2.5	mΩ
\mathbf{R}_{thJC}	thermal resistance junction to cas	е				0.4	K/W
R thCH	thermal resistance case to heatsin	nk			0.1		K/W
P _{tot}	total power dissipation		$T_c = 25^{\circ}C$			310	W
I _{FSM}	max. forward surge current	$t = 10 \text{ ms}; (50 \text{ Hz}), \text{ sine}; V_{R} = 0 \text{ V}$	$T_{VJ} = 45^{\circ}C$			1.60	kA
C	junction capacitance	$V_{R} = 24 V f = 1 MHz$	$T_{VJ} = 25^{\circ}C$		902		pF

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DSA240X200NA

Package	e SOT-227B (minibloc)				Ratings			
Symbol	Definition	Conditions			min.	typ.	max.	Unit
I _{RMS}	RMS current	per terminal					150	A
T _{vj}	virtual junction temperature				-40		150	°C
T _{op}	operation temperature				-40		125	°C
T _{stg}	storage temperature		-40		150	°C		
Weight						30		g
M _D	mounting torque				1.1		1.5	Nm
M _T	terminal torque				1.1		1.5	Nm
d _{Spp/App}	ana ana diatanga ang sufasa katulung diatang akunun		terminal to terminal	10.5	3.2			mm
d _{Spb/Apb}	creepage ustance on sunac	e Siriking distance through an	terminal to backside	8.6	6.8			mm
V	isolation voltage	t = 1 second			3000			V
	t = 1 minute		50/60 Hz, RMS; liso∟ ≤ 1 mA		2500			V

Product Marking



Part description

- D = Diode S = Schottky Diode
- A = low VF 240 = Current Rating [A]

- X = Parallel legs 200 = Reverse Voltage [V] NA = SOT-227B (minibloc)

Ordering	Ordering Number	Marking on Product	Delivery Mode	Quantity	Code No.
Standard	DSA240X200NA	DSA240X200NA	Tube	10	511108

Similar Part	Package	Voltage class
DSS2x101-02A	SOT-227B (minibloc)	200

Equiva	lent Circuits for	Simulation	* on die level	$T_{VJ} = 150^{\circ}C$
	$-R_0$	Schottky		
V _{0 max}	threshold voltage	0.54		V
$\mathbf{R}_{0 \text{ max}}$	slope resistance *	0.6		mΩ

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Outlines SOT-227B (minibloc)



Dim	Millir	neter	Inches		
Dim.	min	max	min	max	
Α	31.50	31.88	1.240	1.255	
В	7.80	8.20	0.307	0.323	
С	4.09	4.29	0.161	0.169	
D	4.09	4.29	0.161	0.169	
Е	4.09	4.29	0.161	0.169	
F	14.91	15.11	0.587	0.595	
G	30.12	30.30	1.186	1.193	
Н	37.80	38.23	1.488	1.505	
J	11.68	12.22	0.460	0.481	
К	8.92	9.60	0.351	0.378	
L	0.74	0.84	0.029	0.033	
M	12.50	13.10	0.492	0.516	
Ν	25.15	25.42	0.990	1.001	
0	1.95	2.13	0.077	0.084	
Ρ	4.95	6.20	0.195	0.244	
Q	26.54	26.90	1.045	1.059	
R	3.94	4.42	0.155	0.167	
S	4.55	4.85	0.179	0.191	
Т	24.59	25.25	0.968	0.994	
U	-0.05	0.10	-0.002	0.004	
V	3.20	5.50	0.126	0.217	
W	19.81	21.08	0.780	0.830	
Ζ	2.50	2.70	0.098	0.106	



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Fig. 1 Max. forward voltage drop characteristics







10

1 <u>=125°C</u>

0.1

0.01

0.001

120

0

I_R

[mA]

T_{VJ}=150°C

.100°C_

75°C=

50°C

-25°C-

50

voltage V_R

100

V_R [V]

0.33

Fig. 2 Typ. reverse current IR versus reverse

0.25

0.17

150

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Data according to IEC 60747and per semiconductor unless otherwise specified

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25.163.2453.0	25.163.4253.0	25.190.2053.0	25.194.3453.0	25.320.4853.1	25.320.5253.1	25.326.3253.1	25.326.3553.1	25.330.1653.1
25.330.4753.1	25.330.5253.1	25.334.3253.1	25.334.3353.1	25.350.2053.0	25.352.4753.1	25.522.3253.0	<u>T483C</u> <u>T484C</u>	<u>T485F</u> <u>T485H</u>
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